

AMENDMENTS TO THE SPECIFICATION

1. Please change the title as follows:

SEMICONDUCTOR DEVICE WITH TRENCH STRUCTURE AND METHOD FOR
MANUFACTURING THE SAME

2. Please change the line 10 of page 6 as follows:

approximately ~~10.m~~ 10 μ m.

3. Please change the line 6 of the page 17 as follows:

thin P-type diffusion layer ~~42~~ 15 with the thickness of about ~~5.m~~ 5 μ m.